



# DCR1300L85

# **Phase Control Thyristor**

Replaces DS5816-4 DS5816-5 October 2023 (LN42827)

### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

## **VOLTAGE RATINGS**

| Part and<br>Ordering<br>Number | Repetitive<br>Peak Voltages<br>VDRM and VRRM<br>(V) | Conditions            |  |
|--------------------------------|---|-----------------------|--|
|                                |   | Tvj = -40°C to 125°C, |  |
| DCR1300L85*                    | 8500  | IDRM = IRRM = 300mA,  |  |
| DCR1300L80                     | 8000  | VDRM, VRRM tp = 10ms  |  |
| DCR1300L75                     | 7500  | VDSM & VRSM =         |  |
| DCR1300L70                     | 7000  | VDRM & VRRM + 100V    |  |
|                                |   | respectively          |  |

Lower voltage grades available.

### ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR1300L85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### **KEY PARAMETERS**

| $\mathbf{V}_{DRM}$ | 8500V    |
|--------------------|----------|
| I <sub>T(AV)</sub> | 1300A    |
| Ітѕм               | 17600A   |
| dV/dt*             | 1500V/μs |
| dl/dt              | 400A/μs  |

<sup>\*</sup> Higher dV/dt selections are available on request

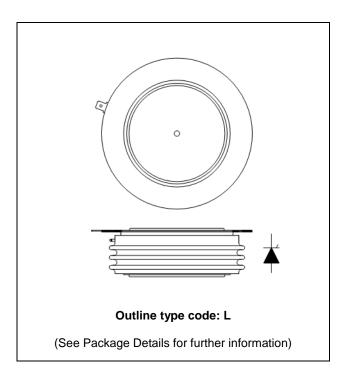


Fig. 1 Package outline

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<sup>\*8200</sup>V @ -40°C, 8500V @ 0°C



## **CURRENT RATINGS**

## T<sub>case</sub> = 60°C unless stated otherwise

| Symbol    | Parameter                            | Test Conditions          | Max. | Units |
|-----------|--------------------------------------|--------------------------|------|-------|
| Double Si | de Cooled                            |                          |      |       |
| IT(AV)    | Mean on-state current                | Half wave resistive load | 1300 | А     |
| IT(RMS)   | RMS value                            | -                        | 2040 | А     |
| lτ        | Continuous (direct) on-state current | -                        | 1970 | А     |

## **SURGE RATINGS**

| Symbol | Parameter                               | Test Conditions                         | Max. | Units             |
|--------|---|---|------|-------------------|
| Ітѕм   | Surge (non-repetitive) on-state current | e current 10ms half sine, Tcase = 125°C |      | kA                |
| l²t    | I2t for fusing                          | V <sub>R</sub> = 0                      | 1.55 | MA <sup>2</sup> s |

## THERMAL AND MECHANICAL RATINGS

| Symbol   | Parameter                             | Test Condition           | Min.        | Max. | Units |       |
|----------|---------------------------------------|--------------------------|-------------|------|-------|-------|
|          |                                       | Double side cooled       | DC          | -    | 11.7  | °C/kW |
| Rth(j-c) | Thermal resistance - junction to case | Cingle side socied       | Anode DC    | -    | 18.6  | °C/kW |
|          |                                       | Single side cooled       | Cathode DC  | -    | 32.9  | °C/kW |
| D        |                                       | Clamping force 37kN      | Double side | -    | 2.5   | °C/kW |
| Rth(c-h) | Thermal resistance - case to heatsink | (with mounting compound) | Single side | -    | 5.0   | °C/kW |
| Tvj      | Virtual junction temperature          | Blocking Vdrm / Vrrm     |             | -    | 125   | °C    |
| Tstg     | Storage temperature range             |                          |             | -55  | 125   | °C    |
| Fm       | Clamping force                        |                          |             | 33   | 41    | kN    |

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## **DYNAMIC CHARACTERISTICS**

| Symbol         | Parameter                                     | Test Condition  | ns                 | Min. | Max. | Units |
|----------------|---|---|--------------------|------|------|-------|
| IRRM/IDRM      | Peak reverse and off-state current            | At VRRM/VDRM, Tcase = 125°C   | ;                  | -    | 300  | mA    |
| Vтм            | Instantaneous forward voltage                 | At 4000A peak, Tj = 125°C   |                    | 3.90 | 4.40 | V     |
| dV/dt          | Max. linear rate of rise of off-state voltage | To 67% VDRM, Tj = 125°C, ga   | ate open           | -    | 1500 | V/µs  |
| dl/dt          | Rate of rise of on-state current              | From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub> Gate source 30V, 10Ω                               | Repetitive<br>50Hz | -    | 200  | A/µs  |
| di/dt          | Nate of fise of on-state current              | tr < 0.5µs, Tj = 125°C  | Non-repetitive     | -    | 400  | A/µs  |
| Varia          | Threshold voltage - Low level                 | 500A to 2000A at Tcase = 125°C  |                    | -    | 1.18 | V     |
| <b>V</b> т(то) | Threshold voltage - High level                | 2000A to 7000A at Tcase = 125°C   |                    | -    | 1.32 | V     |
| _              | On-state slope resistance - Low level         | 500A to 2000A at Tcase = 125°C  |                    | -    | 0.84 | mΩ    |
| ľΤ             | On-state slope resistance - High level        | 2000A to 7000A at Tcase = 125°C   |                    | -    | 0.77 | mΩ    |
| tgd            | Delay time                                    | $V_D = 67\% \ V_{DRM}$ , gate source 30V, $10\Omega$ $t_T = 0.5 \mu s$ , $T_j = 25 ^{\circ} C$        |                    | 1    | 3    | μs    |
| tq             | Turn-off time                                 | T <sub>j</sub> = 125°C, V <sub>R</sub> = 200V, dI/dt = 1A/μs,<br>dV <sub>DR</sub> /dt = 20V/μs linear |                    | -    | 1200 | μs    |
| Qs             | Stored charge                                 | Iτ = 2000A, T <sub>j</sub> = 125°C, dI/dt = 1A/μs,<br>VR(peak) ~ 3900V, VRM ~ 2600V                   |                    | 4290 | 5940 | μC    |
| IRR            | Reverse recovery current                      |   |                    | 47   | 54   | А     |
| lL .           | Latching current                              | Tj = 25°C, VD = 5V  |                    | -    | 3    | А     |
| lн             | Holding current                               | Tj = 25°C, Rg-κ = ∞, Iτм = 50   | 0A, Iτ = 5A        | -    | 300  | mA    |

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## **GATE TRIGGER CHARACTERISTICS AND RATINGS**

| Symbol          | Parameter                | Test Conditions            | Max. | Units |
|-----------------|--------------------------|----------------------------|------|-------|
| <b>V</b> GT     | Gate trigger voltage     | VDRM = 5V, Tcase = 25°C    | 1.5  | V     |
| V <sub>GD</sub> | Gate non-trigger voltage | At 50% VDRM, Tcase = 125°C | 0.4  | V     |
| lgт             | Gate trigger current     | VDRM = 5V, Tcase = 25°C    | 350  | mA    |
| IGD             | Gate non-trigger current | At 50% VDRM, Tcase = 125°C | 15   | mA    |

## **CURVES**

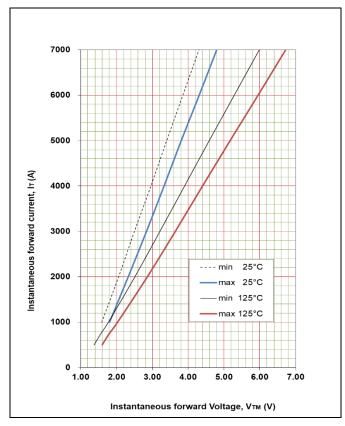


Fig. 2 Maximum & minimum on-state characteristics

## **VTM EQUATION**

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.937135

B = 0.030939

C = 0.000730

D = 0.004730

These values are valid for  $T_j = 125^{\circ}C$  for  $I_{T}$  500A to 7000A

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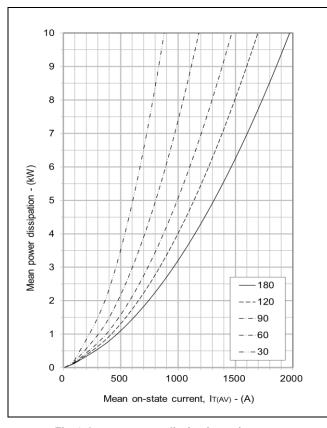


Fig. 3 On-state power dissipation - sine wave

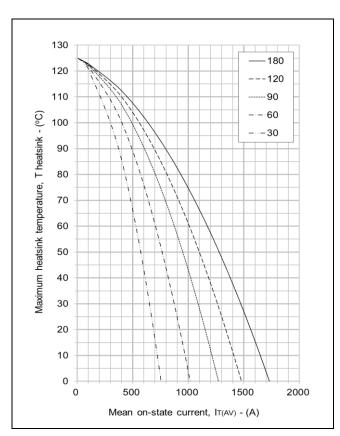


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

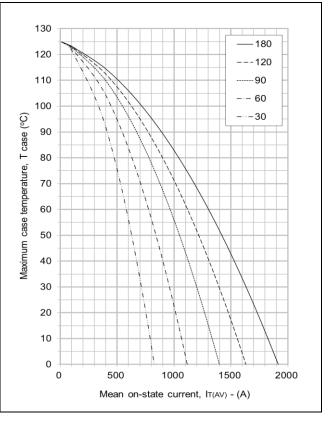


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

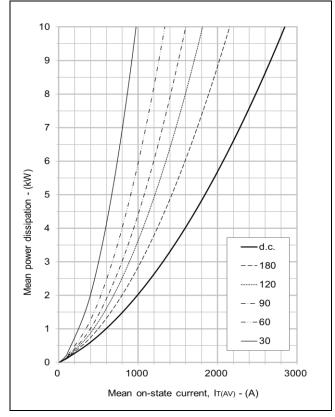


Fig. 6 On-state power dissipation - rectangular wave

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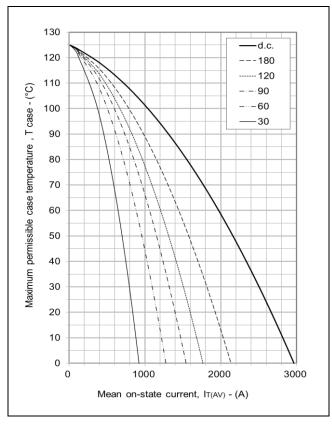
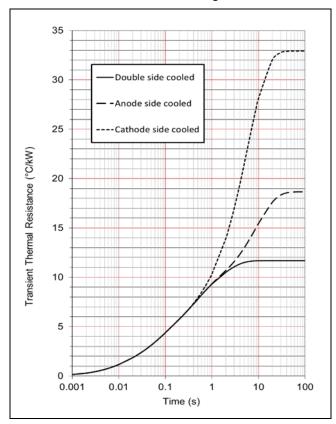


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



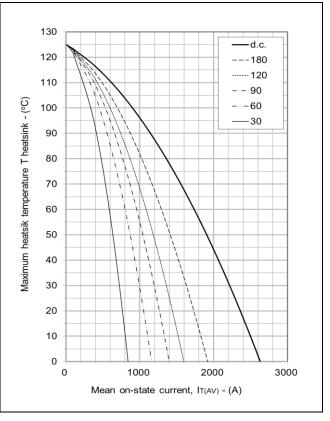


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

|                   |           | 1     | 2     | 3     | 4      |
|-------------------|-----------|-------|-------|-------|--------|
| Double side       | Ri(°C/kW) | 0.834 | 2.607 | 4.207 | 4.041  |
| cooled            | Ti(s)     | 0.009 | 0.053 | 0.331 | 1.612  |
| Anode side cooled | Ri(°C/kW) | 0.965 | 2.831 | 4.943 | 9.909  |
|                   | Ti(s)     | 0.010 | 0.063 | 0.420 | 8.908  |
| Cathode side      | Ri(°C/kW) | 0.929 | 2.937 | 2.358 | 26.683 |
| cooled            | Ti(s)     | 0.009 | 0.062 | 0.309 | 5.853  |

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$  Conduction

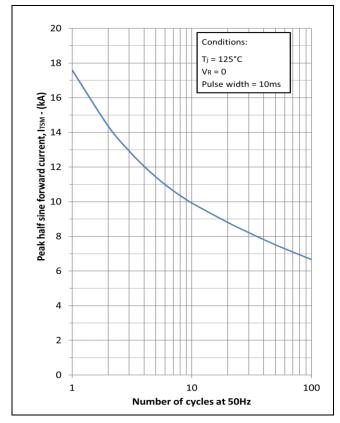
Tables show the increments of thermal resistance R  $_{\text{th}(j-q)}$  when the device operates at conduction angles other than d.c.

|     | Double side co | oling | Anode Side Cooling |                 |       | Ca                  | thode Side | d Cooling           |  |  |              |                  |
|-----|----------------|-------|--------------------|-----------------|-------|---------------------|------------|---------------------|--|--|--------------|------------------|
|     | $\Delta Z_h$ ( | (z)   |                    | $\Delta Z_h(z)$ |       | $\Delta Z_{f_1}(z)$ |            | $\Delta Z_{f_1}(z)$ |  |  | $\Delta Z_i$ | <sub>h</sub> (Z) |
| θ°  | sine.          | rect. | θ°                 | sine.           | rect. | θ°                  | sine.      | rect.               |  |  |              |                  |
| 180 | 1.45           | 0.98  | 180                | 1.43            | 0.97  | 180                 | 1.44       | 0.97                |  |  |              |                  |
| 120 | 1.68           | 1.40  | 120                | 1.66            | 1.39  | 120                 | 1.66       | 1.39                |  |  |              |                  |
| 90  | 1.93           | 1.64  | 90                 | 1.90            | 1.62  | 90                  | 1.91       | 1.63                |  |  |              |                  |
| 60  | 2.16           | 1.90  | 60                 | 2.12            | 1.88  | 60                  | 2.14       | 1.89                |  |  |              |                  |
| 30  | 2.34           | 2.19  | 30                 | 2.30            | 2.15  | 30                  | 2.31       | 2.17                |  |  |              |                  |
| 15  | 2.42           | 2.34  | 15                 | 2.37            | 2.30  | 15                  | 2.39       | 2.31                |  |  |              |                  |

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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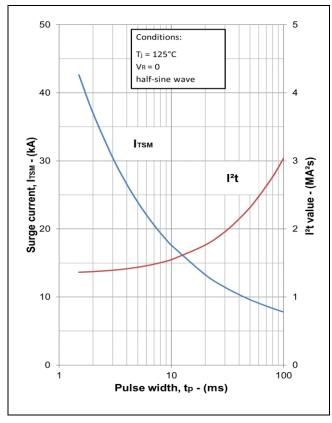


Fig. 10 Multi-cycle surge current

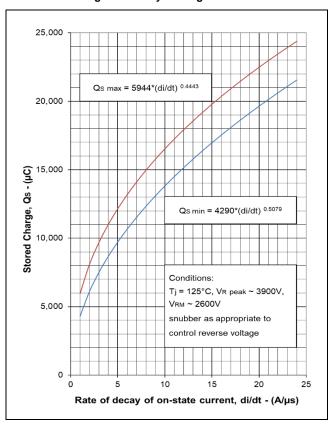


Fig. 12 Reverse recovery charge

Fig. 11 Single-cycle surge current

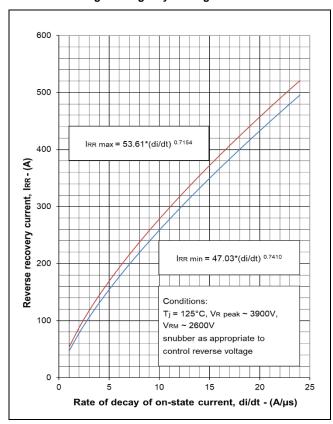


Fig. 13 Reverse recovery current

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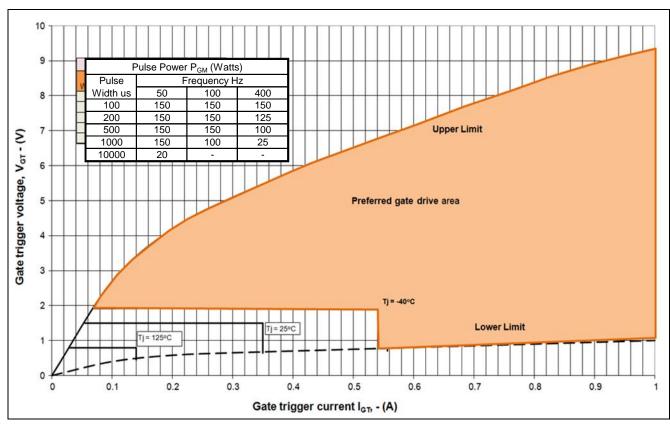


Fig. 14 Gate characteristics

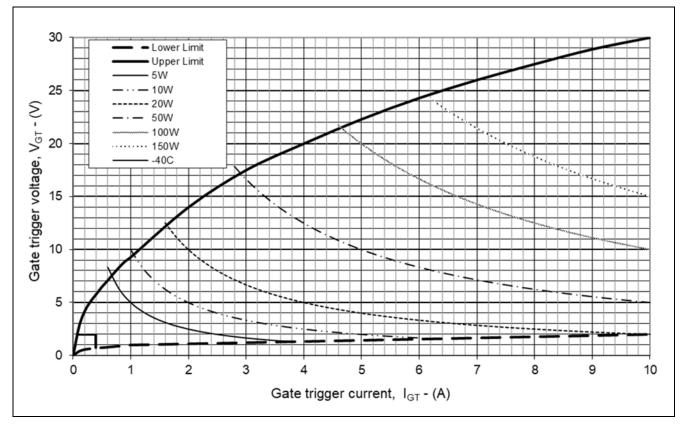


Fig. 15 Gate characteristics

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### **PACKAGE DETAILS**

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

## DO NOT SCALE

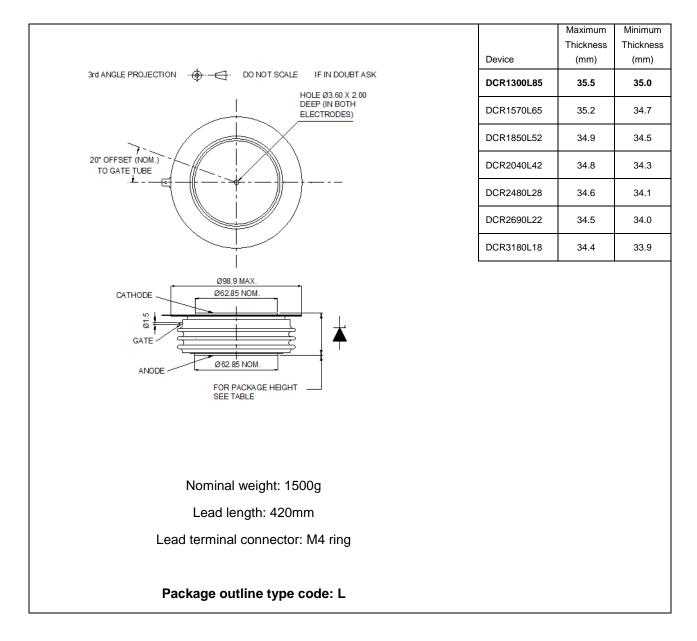


Fig. 16 Package outline

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